TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (Ultra-High-speed U-MOSIII)

# **TPCA8107-H**

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications CCFL Inverter Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge:  $Q_{SW} = 9.7 \text{ nC (typ.)}$
- Low drain-source ON-resistance: RDS (ON) =  $24 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 14 \text{ S (typ.)}$
- Low leakage current:  $IDSS = -10 \mu A (max) (VDS = -40 V)$
- Enhancement mode:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V } (V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA})$

### Absolute Maximum Ratings (Ta = 25°C)

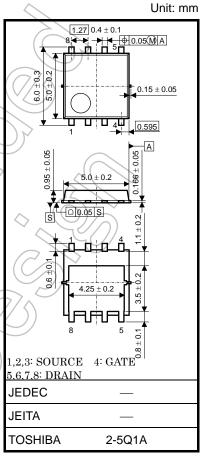
Characte	ristic	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	-40	V	
Drain-gate voltage (R	GS = 20 kΩ)	V <sub>DGR</sub>	-40	N	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	I <sub>D</sub> -7.5		A	
Diam carrent	Pulsed (Note 1)	IDP	-30	$\wedge$	
Drain power dissipation	on $(Tc = 25^{\circ}C)$	(PD))	30	_//w	
Drain power dissipation	on (t = 10 s) (Note 2a)	P <sub>D</sub>	2.8 W		
Drain power dissipation	on (t = 10 s) (Note 2b)	PD	1.6	W	
Single-pulse avalanch	ne energy (Note 3)	EAS	26	mJ	
Avalanche current		I <sub>AR</sub>	-7.5	Α	
Repetitive avalanche energy (Tc = 25°C) (Note 4)		EAR	1.9	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

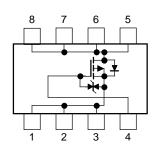
operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

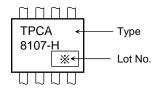
#### **Circuit Configuration**



#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case $({\rm Tc}=25^{\circ}{\rm C})$	R <sub>th (ch-c)</sub>	4.17	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

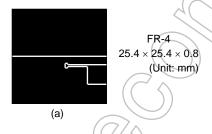
### Marking (Note 5)

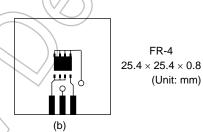


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3:  $V_{DD} = -24 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial),  $L = 500 \ \mu\text{H}$ ,  $R_G = 25 \ \Omega$ ,  $I_{AR} = -7.5 \ A$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)

Week of manufacture

(01 for the first week of the year, continuing up to 52 or 53)

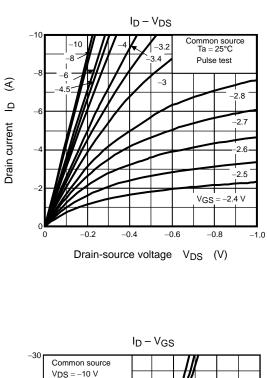
Year of manufacture (The last digit of the year)

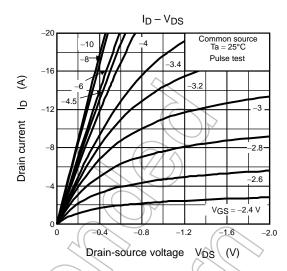
## Electrical Characteristics (Ta = 25°C)

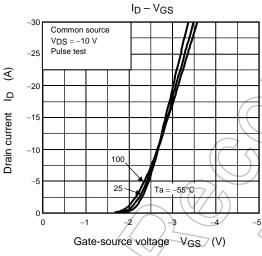
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cutoff curre	nt	I <sub>DSS</sub>	V <sub>DS</sub> = -40 V, V <sub>GS</sub> = 0 V		_	-10	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-40	_	_	· v
		V (BR) DSX	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	-20	_	_	
Gate threshold vo	oltage	$V_{th}$	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	-0.8	) /_	-2.0	V
Drain-source ON-resistance		R <sub>DS</sub> (ON)	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.8 A	) <u> </u>	29	37	- mΩ
			V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.8 A	$\mathcal{D}$	24	30	
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -3.8 \text{ A}$	7	14	_	S
Input capacitance	•	C <sub>iss</sub>		_	1190	_	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	170	_	pF
Output capacitance		C <sub>oss</sub>		/	250	$\rightarrow$	
Switching time	Rise time	t <sub>r</sub>	V <sub>GS</sub> 0 V   I <sub>D</sub> = -3.8 A   O V <sub>OUT</sub>	-(	5	> -	
	Turn-on time	t <sub>on</sub>	-10 V C C C C C S S S S S S S S S S S S S S		12	_	
	Fall time	t <sub>f</sub>	R = 1	$(\mathcal{E})$	12	_	ns
	Turn-off time	t <sub>off</sub>	$V_{DD} \approx -20 \text{ V}$ Duty $\leq 1\%$ , $t_W = 10 \mu\text{s}$	) —	43	_	
Total gate charge (gate-source plus gate-drain)			$V_{DD} \approx -32 \text{ V}, V_{GS} = -10 \text{ V},$ $I_D = -7.5 \text{ A}$		27		
		Q <sub>g</sub>	$V_{DD} \approx -32 \text{ V, } V_{GS} = -5 \text{ V,}$ $I_{D} = -7.5 \text{ A}$	_	15	_	nC
Gate-source char	ge 1	Q <sub>gs1</sub>		_	3.2	_	
Gate-drain ("Miller") charge		Q <sub>gd</sub>	$V_{DD} \approx -32 \text{ V}, V_{GS} = -10 \text{ V},$	_	8.1	_	
Gate switch charg	ge (	Q <sub>SW</sub>	$I_D = -7.5 \text{ A}$	_	9.7	_	

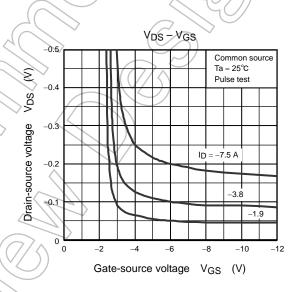
# Source-Drain Ratings and Characteristics (Ta = 25°C)

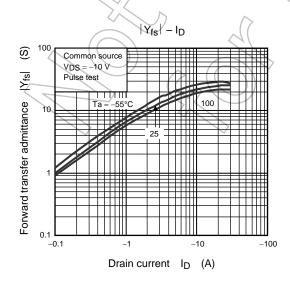
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse	(Note 1)	DRP	_	_	_	-30	Α
Forward voltage (diode)		VDSF	$I_{DR} = -7.5 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V

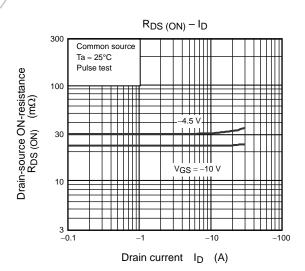






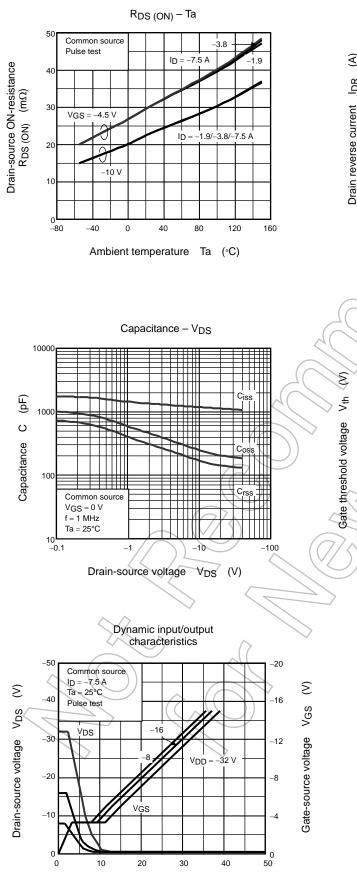


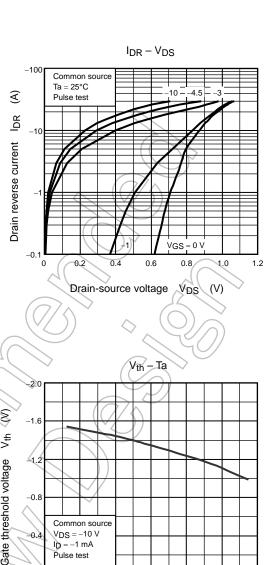




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160





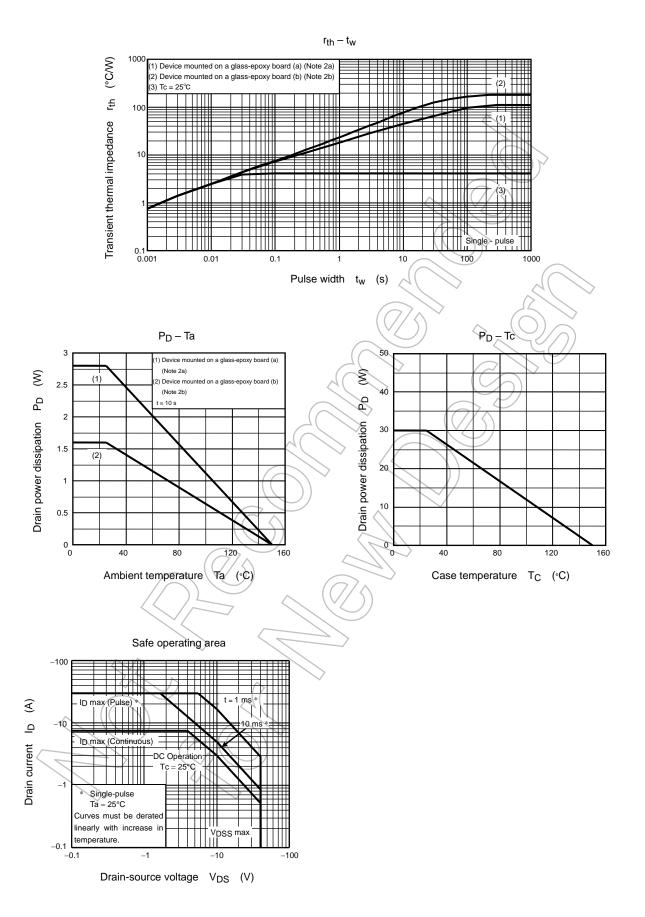
-80

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Total gate charge Q<sub>g</sub> (nC)

2008-10-06

Ambient temperature Ta (°C)



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